

L Number	Hits	Search Text	DB	Time stamp
-	116	(nitride adj3 tunnel\$3) with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 17:23
-	25	((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:40
-	3	((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron) and (charge adj3 trap\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:44
-	854	(first adj3 voltage) and (substrate adj3 ground)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:45
-	161	((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:46
-	5	((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source) and ((hot adj3 electron) with channel) and (inject\$3 same (charge with trap\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:19
-	1756	SONOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:20
-	7	SONOS and (nitride adj2 tunnel\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:21
-	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:26
-	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive ground gate substrate drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:27
-	0	(drain with (positive adj2 (voltage bias))) and (gate with (positive adj2 (voltage bias))) and (substrate with ground\$3) and (source with ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 17:45
-	58434	eras\$3 and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 17:27
-	1	(eras\$3 and memory) and (nitride adj2 tunneling adj2 layer) and (charge near2 trap\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 17:28

-	1	(eras\$3 and memory) and (nitride adj2 tunneling adj2 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:29
-	101	(eras\$3 and memory) and ((nitride adj2 tunneling adj2 layer) SONOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:29
-	35	(eras\$3 and memory) and ((nitride adj2 tunneling adj2 layer) SONOS) and (charge near2 trap\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:31
-	33	((eras\$3 and memory) and ((nitride adj2 tunneling adj2 layer) SONOS) and (charge near2 trap\$4)) and drain and source and substrate and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:32
-	0	(drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (substrate with ground\$3) and (source with ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:48
-	2315	(drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:49
-	0	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate near3 ground\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:50
-	1044	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:50
-	0	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (substrate near3 ground\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:50
-	469	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate same ground\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:51
-	354	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate with ground\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:52
-	9	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate with ground\$3)) and SONOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:56
-	9	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate with ground\$3)) and SONOS and eras\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:59

- Drafts
- Pending
- Active
 - L1: (1190) (non-volatile nonvolatile
 - L2: (369) L1 and ((positive adj3 (bi
 - L3: (616) L1 and ((positive adj3 (bi
 - L4: (681) L1 and (ground near3 source
 - L5: (206) L2 and L3 and 14
 - L6: (69) ((positive adj3 (bias poten
 - L7: (26) L1 and L6
 - L8: (138) (((positive high) adj3 (bi
 - L9: (43) L1 and L8
- Failed
- Saved
- Favorites
- Tagged (12)
- UDC
- Queue
- Trash

DBs: USPAT-US-PPGPUB-EPO-JPO-DERWENT:IBM-TDB
 Purge

Default operator: OR
 Highlight all hit terms initially

L1 and L8

BR5 term
IS&R term
Image
Text
HTML

	Current OR	Current XRef	Retrieval C	Inventor	S	C										Image	Doc	DIS	PT
1	365/185.29			Choi, Ki-Hwan	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020060929			<input checked="" type="checkbox"/>							
2	714/766			Yada, Naoki et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020032891			<input checked="" type="checkbox"/>							
3	365/185.28	257/E29.128; 257/E29.309;		Bergemont, Albert et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6327187			<input checked="" type="checkbox"/>							
4	365/185.29	365/185.14; 365/185.18;		Sung, Hung-Cheng et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6005809			<input checked="" type="checkbox"/>							
5	365/185.07	365/182; 365/185.25;		Okumura, Koichiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4635229			<input checked="" type="checkbox"/>							
6	438/323			Eliyahu, Ron et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020132436			<input type="checkbox"/>
7	257/296			Kim, Dong-Jun et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020100926			<input type="checkbox"/>

HD Details HTML

Results

NUM